

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-a)	Junction to ambient		60	°C/W
Rth (j-c) DC	Junction to case for DC	BTA	4.4	°C/W
		BTB	3.3	
Rth (j-c) AC	Junction to case for 360° conduction angle (F = 50 Hz)	BTA	3.3	°C/W
		BTB	2.5	

GATE CHARACTERISTICS (maximum values)

$P_G (AV) = 1W$ $P_{GM} = 10W$ ($t_p = 20 \mu s$) $I_{GM} = 4A$ ($t_p = 20 \mu s$) $V_{GM} = 16V$ ($t_p = 20 \mu s$).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Suffix		Unit
					TW	SW	
I _{GT}	V _D =12V (DC) R _L =33Ω	T _j =25°C	I-II-III	MAX	5	10	mA
V _{GT}	V _D =12V (DC) R _L =33Ω	T _j =25°C	I-II-III	MAX	1.5		V
V _{GD}	V _D =V _{DRM} R _L =3.3kΩ	T _j =110°C	I-II-III	MIN	0.2		V
tgt	V _D =V _{DRM} I _G = 40mA dI _G /dt = 0.5A/μs	T _j =25°C	I-II-III	TYP	2		μs
I _L	I _G =1.2 I _{GT}	T _j =25°C	I-III	TYP	8	15	mA
			II		15	25	
I _H *	I _T = 100mA gate open	T _j =25°C		MAX	15	25	mA
V _{TM} *	I _{TM} = 8.5A tp= 380μs	T _j =25°C		MAX	1.75		V
I _{DRM} I _{RRM}	V _{DRM} Rated V _{RRM} Rated	T _j =25°C		MAX	0.01		mA
		T _j =110°C		MAX	1		
dV/dt *	Linear slope up to V _D =67%V _{DRM} gate open	T _j =110°C		MIN	20	50	V/μs
(dI/dt) _c *	dV/dt= 0.1V/μs	T _j =110°C		MIN	2.7	3.5	A/ms
	dV/dt= 20V/μs			MIN	1.3	2.7	

* For either polarity of electrode A₂ voltage with reference to electrode A₁.

ORDERING INFORMATION

Package	I _T (RMS)	V _{DRM} / V _{RRM}	Sensitivity Specification	
	A	V	TW	SW
BTA (Insulated)	6	400	X	X
		600	X	X
		700	X	X
BTB (Uninsulated)		400	X	X
		600	X	X
		700	X	X

Fig.1 : Maximum RMS power dissipation versus RMS on-state current ($F=50\text{Hz}$).
(Curves are cut off by $(di/dt)_c$ limitation)

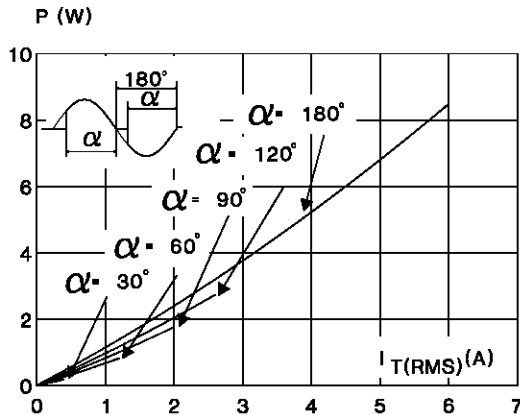


Fig.3 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTB).

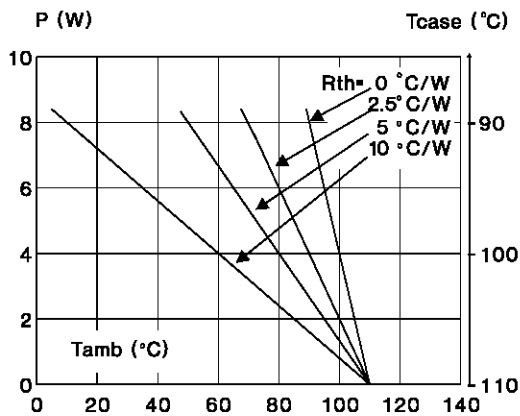


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTA).

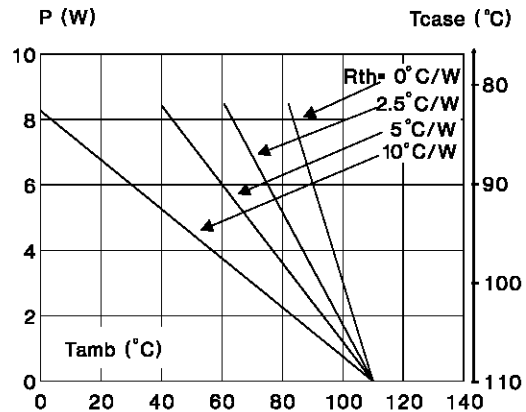


Fig.4 : RMS on-state current versus case temperature.

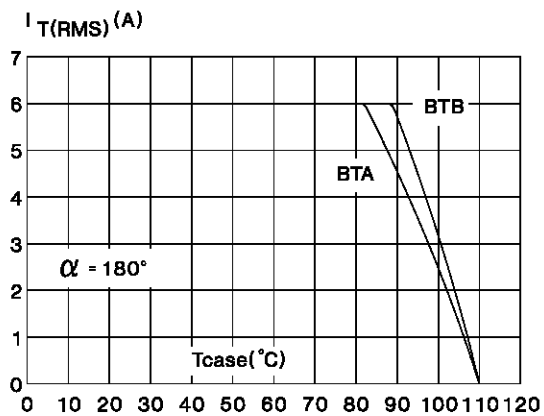


Fig.5 : Relative variation of thermal transient impedance versus pulse duration.

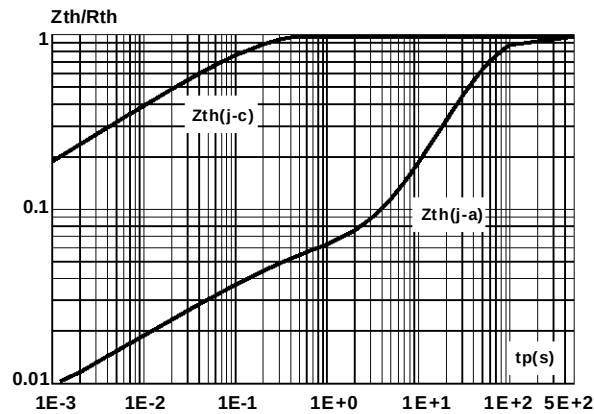


Fig.7 : Non Repetitive surge peak on-state current versus number of cycles.

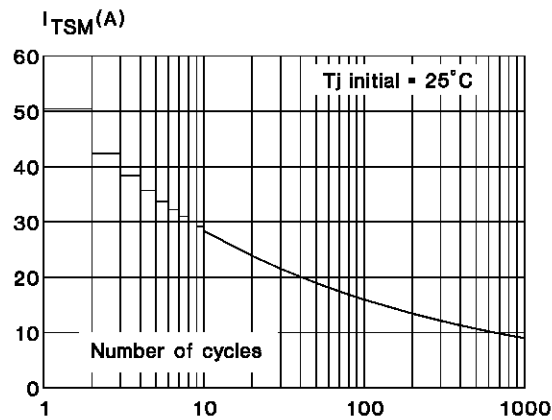


Fig.9 : On-state characteristics (maximum values).

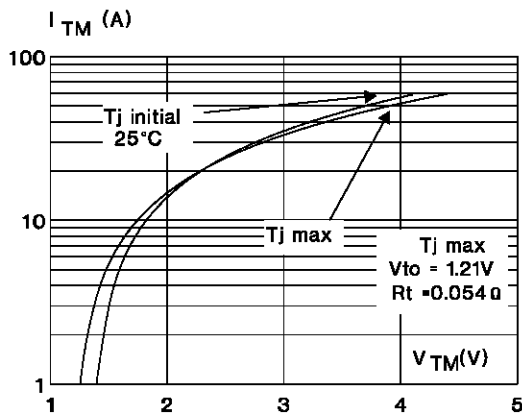


Fig.6 : Relative variation of gate trigger current and holding current versus junction temperature.

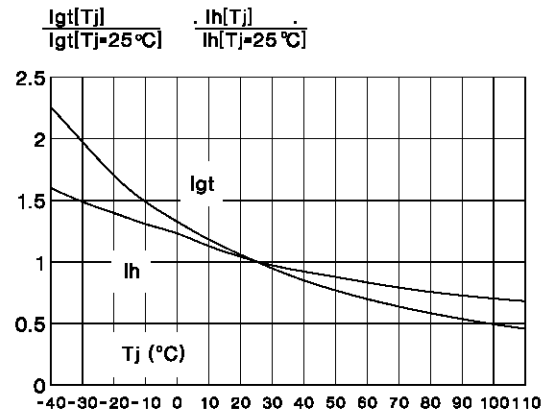


Fig.8 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t \leq 10ms$, and corresponding value of I^2t .

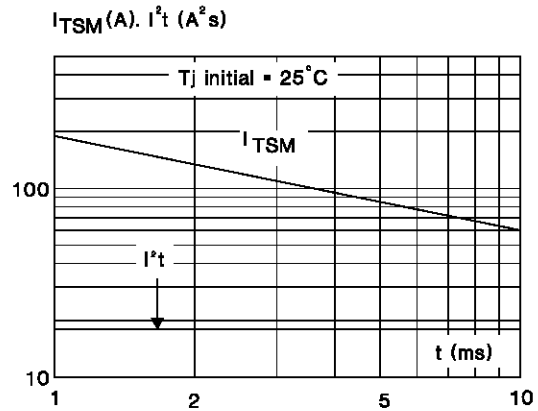
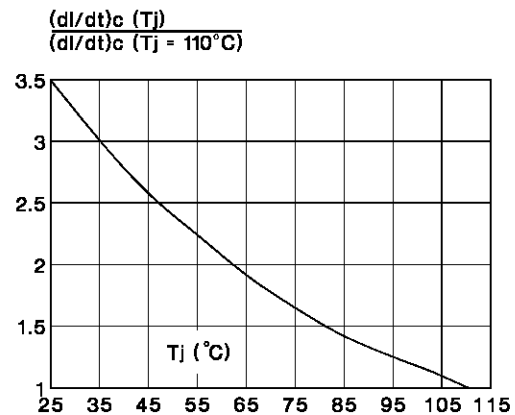
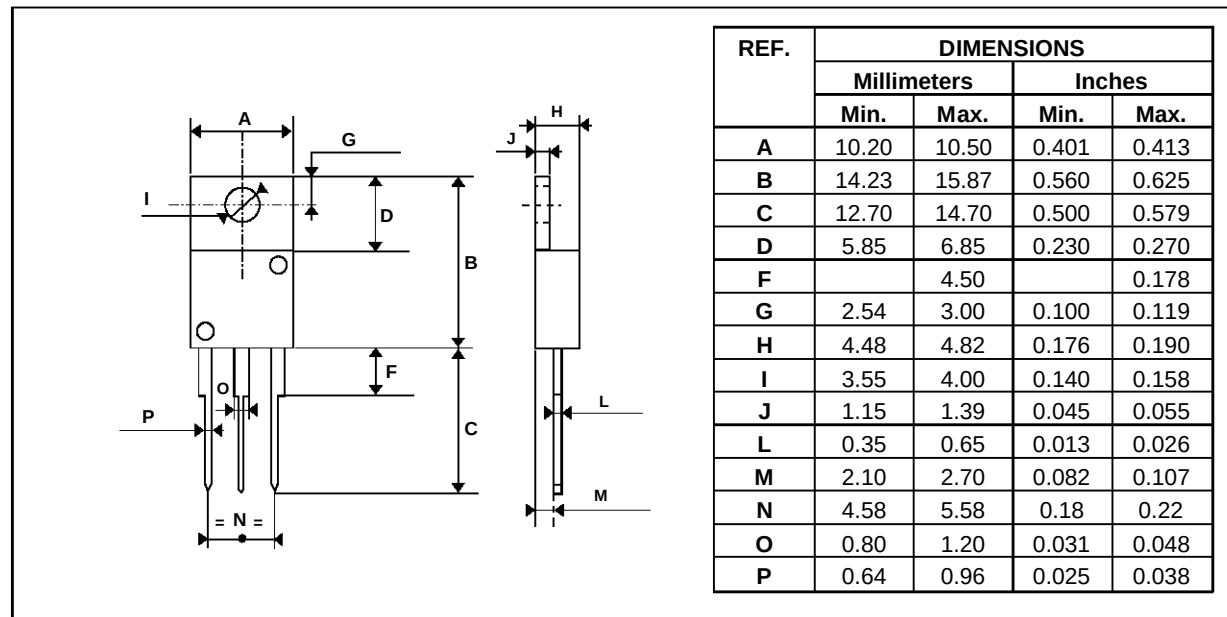


Fig.10 : Relative variation of $(dl/dt)_c$ versus junction temperature.



PACKAGE MECHANICAL DATA

TO220AB Plastic



Cooling method : C

Marking : type number

Weight : 2.3 g

Recommended torque value : 0.8 m.N.

Maximum torque value : 1 m.N.

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